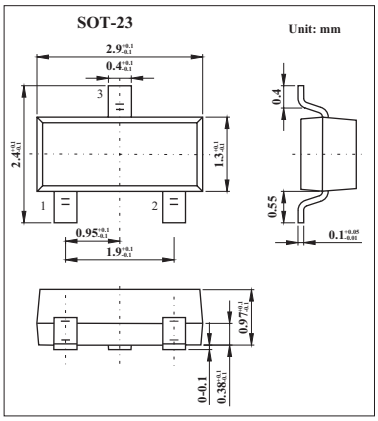
Sillicon Epitaxial Schottky Barrier Diode

1SS351



Features

- Series connection of 2 elements in a small-sized package facilitates high-density mounting and permits 1SS351-applied equipment to be made smaller.
- Small interterminal capacitance (C=0.69pF typ).
- Small forward voltage (V_F=0.23V max).

Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Value	Unit
Reverse Voltage	V_R	5	V
Forward Current	I_F	30	mA
Junction Temperature	T_j	125	℃
Storage temperature	T_{stg}	-55 to +125	℃

Electrical Characteristics Ta = 25℃

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Forward Voltage	V_F	I_F = 1 mA			0.23	V
Forward Current	I_F	V_F = 0.5 V	30			mA
Reverse Current	I_R	V_R = 0.5 V			25	μA
Interterminal Capacitance	C	V_R = 0.2 V, f = 1 MHz		0.69	0.9	pF

Marking

Marking	CH